2SD2061

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0553 I ṂṂ Ł QSQ ÆṀ ч s ‖ ⁊ Silicon NPN transistor in a TO-220F Plastic Package.

/ Features

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Low $V_{CE(sat)}$,excellent DC current gain characteristics, P_C=30W,wide SOA.

/ Applications

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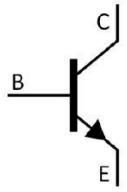
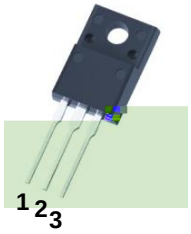
General Purpose Power Amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

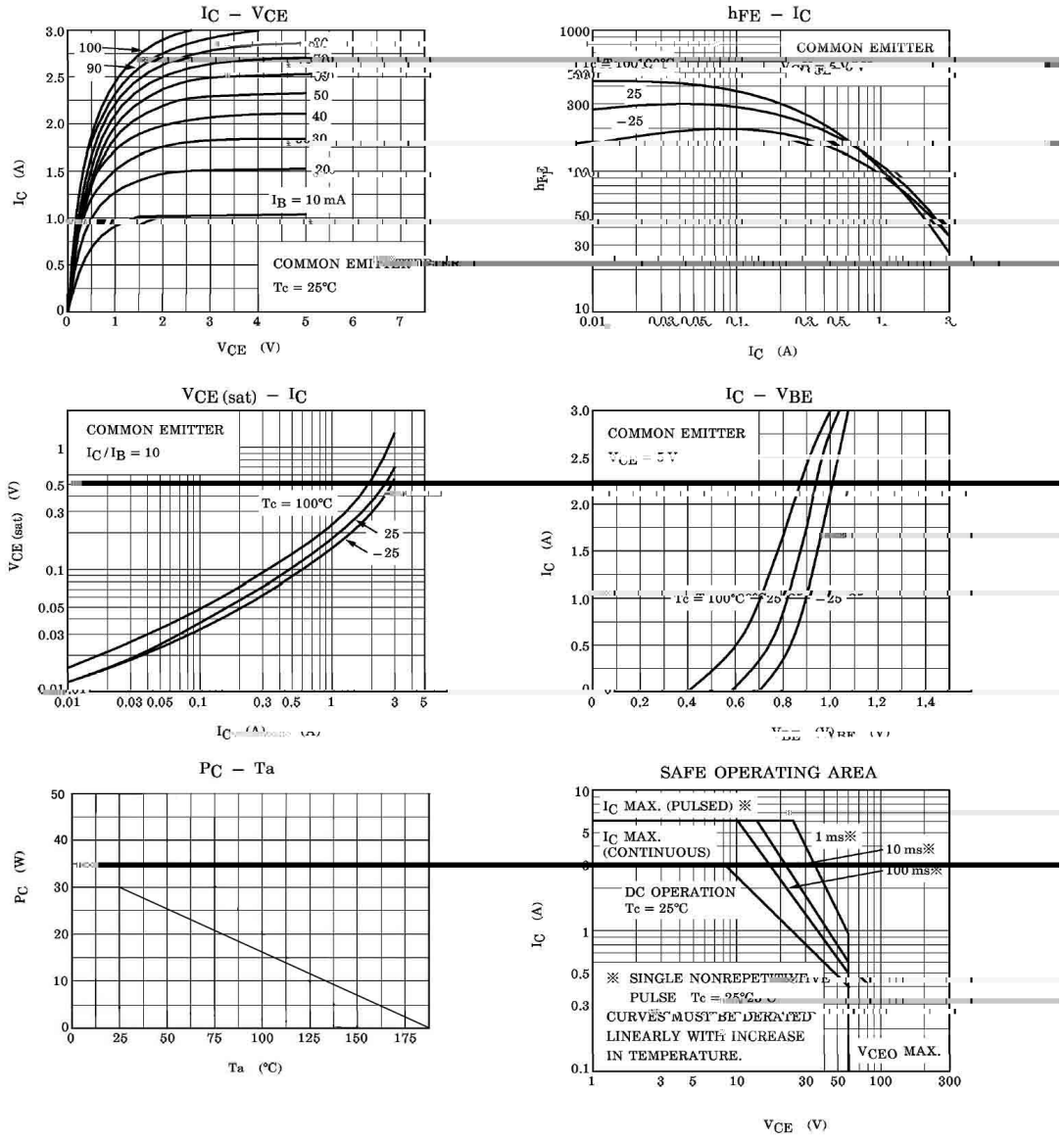
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	E	F
h_{FE} Range	100 200	160 320

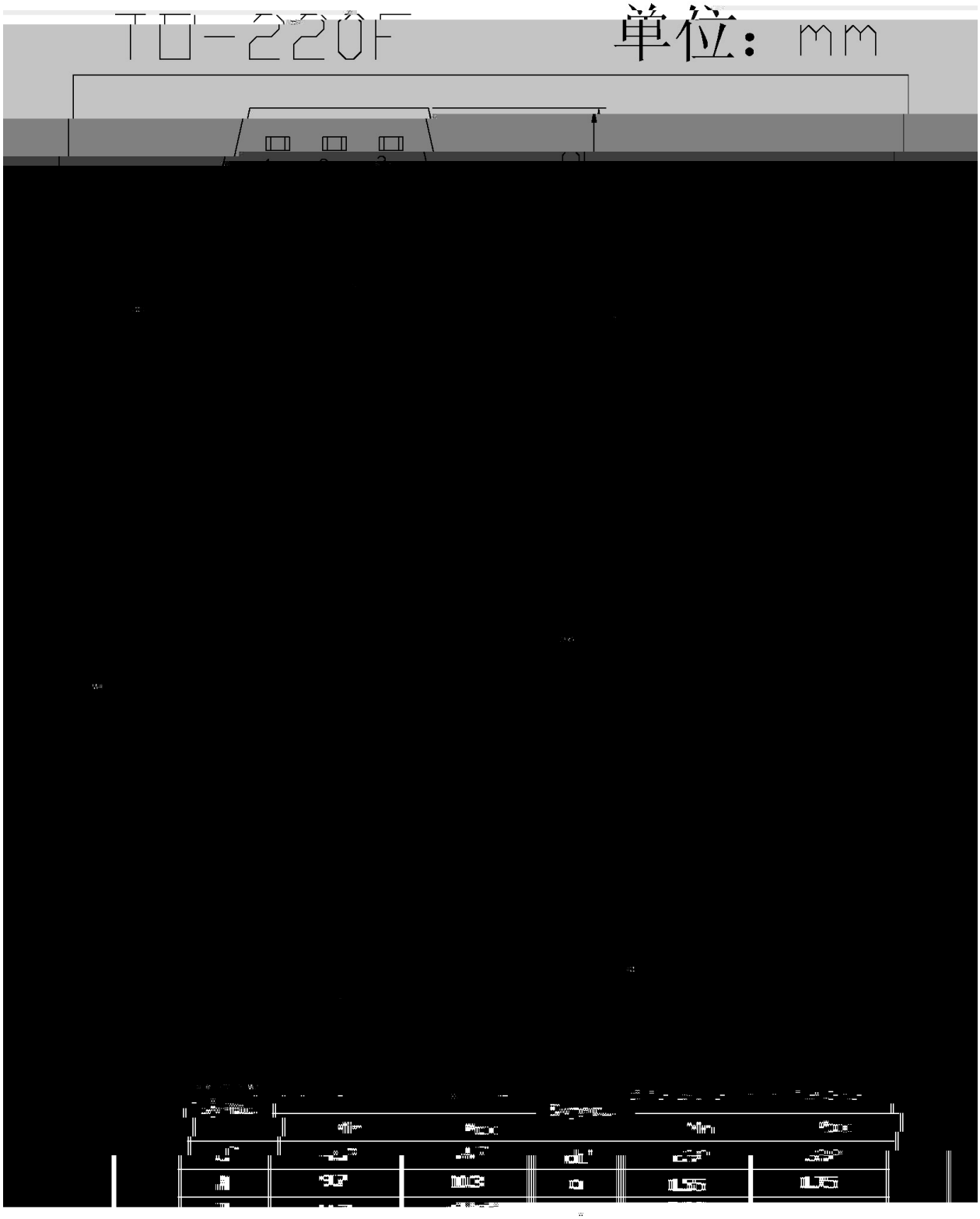
v ̈Ω̣ Parameter	ɬ N Symbol	̈Ω̣Ö Rating	D Ɉ Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	3.0	A
Peak Collector Current	I_{CM}	6.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω̣ Parameter	ɬ N Symbol	⊥⊥ ;ɬ Ţ Test Conditions	ω̣ ṇ Ö Min	Ɛ ʒ Ö Typ	ω̣ ᶻ Ö Max	D Ɉ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50 A	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50 A	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=60V I_E=0			10	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			10	A
DC Current Gain	h_{FE}	V_{CE}=5.0V I_C=500mA	100		320	

/ Electrical Characteristic Curve



/ Package Dimensions



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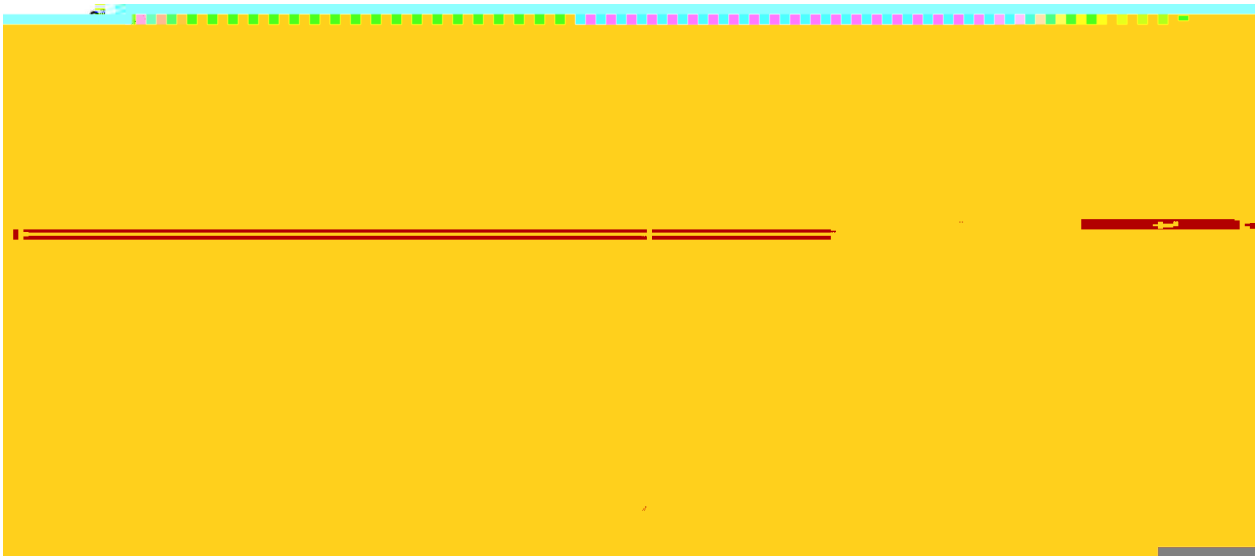
( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 ǂ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˋY ⺈ ⺮ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ھ ỷ ⺮ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

ˋΩ ţ γ Ł / BULK

Package Type	Units					Dimension		(unit mm^3)